



AOS Semiconductor Product Reliability Report

AOD407 rev C

Plastic Encapsulated Device

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This AOS product reliability report summarizes the qualification result for AOD407. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOD407 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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I. Product Description:

The AOD407 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and low gate resistance. With the excellent thermal resistance of the DPAK package, this device is well suited for high current load applications.

- RoHS Compliant
- Halogen Free

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted			
Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	$T_C=25^\circ\text{C}$	-12
		$T_C=100^\circ\text{C}$	-10
Pulsed Drain Current ^C	I_{DM}	-30	A
Avalanche Current ^C	I_{AR}	-12	A
Repetitive avalanche energy $L=0.1\text{mH}$ ^C	E_{AR}	23	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	50
		$T_C=100^\circ\text{C}$	25
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	2.5
		$T_A=70^\circ\text{C}$	1.6
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics					
Parameter	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	16.7	25	$t \leq 10\text{s}$	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A				Steady-State	$^\circ\text{C/W}$
Maximum Junction-to-Case ^B	$R_{\theta JC}$	2.5	3	Steady-State	$^\circ\text{C/W}$



II. Die / Package Information:

Process	AOD407 Standard sub-micron Low voltage P channel process
Package Type	3 leads TO252
Lead Frame	Bare Cu
Die Attach	Soft solder
Bond wire	G: Au 1.3mils; S: Al 12mils
Mold Material	Epoxy resin with silica filler
Flammability Rating	UL-94 V-0
Backside Metallization	Ti / Ni / Ag
Moisture Level	Up to Level 1 *

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AOD407

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	168hr 85°c /85%RH +3 cycle reflow@260 c	-	9 lots	1210pcs	0
HTGB	Temp = 150°c , Vgs=100% of Vgsmax	168 / 500 hrs 1000 hrs	6 lots (Note A*)	492pcs 77+5 pcs / lot	0
HTRB	Temp = 150°c , Vds=80% of Vdsmax	168 / 500 hrs 1000 hrs	6 lots (Note A*)	492pcs 77+5 pcs / lot	0
HAST	130 +/- 2°c , 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	9 lots (Note B**)	495pcs 50+5 pcs / lot	0
Pressure Pot	121°c , 29.7psi, 100%RH	96 hrs	5 lots (Note B**)	275pcs 50+5 pcs / lot	0
Temperature Cycle	-65°c to 150°c , air to air,	250 / 500 cycles	8 lots (Note B**)	440pcs 50+5 pcs / lot	0

III. Result of Reliability Stress for AOD407

Continues

DPA	Internal Vision Cross-section X-ray	NA	5 5 5	5 5 5	0
CSAM		NA	5	5	0
Bond Integrity	Room Temp 150°C bake 150°C bake	0hr 250hr 500hr	40 40 40	40 wires 40 wires 40 wires	0
Solderability	245°C	5 sec	15	15 leads	0
Solder dunk	260°C	10secs 3 cycles	1	30 units	0

Note A: The HTGB and HTRB reliability data presents total of available AOD407 burn-in data up to the published date.

Note B: The pressure pot, temperature cycle and HAST reliability data for AOD407 comes from the AOS generic package qualification data.

IV. Reliability Evaluation

FIT rate (per billion): 9

MTTF = 12331 years